# **MAZWxxxHG Series**

### Silicon planar type

For surge absorption circuit

#### ■ Features

• Two elements anode-common type

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol Rating		Unit	
Total power dissipation *	P <sub>tot</sub>	150	mW	
Junction temperature	$T_{j}$	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

Note) \*: P<sub>tot</sub> = 150 mW achieved with a printed circuit board.

#### Package

- Code
  - SSSMini3-F2
- Pin Name
  - 1: Cathode 1
  - 2: Cathode 2
  - 3: Anode 1, 2

#### ■ Internal Connection



#### ■ Common Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

Parameter	Symbol	6.	Conditions	Min Typ Max	Unit
Zener voltage *	$V_{\rm Z}$	Iz	Specified value —	26 / 60	V
Zener rise operating resistance	R <sub>ZK</sub>	Iz	Specified value	Refer to the list of the electrical characteristics	Ω
Zener operating resistance	R <sub>Z</sub>	Iz	Specified value	within part numbers	Ω
Reverse current	$I_R$	V <sub>R</sub>	Specified value		μΑ

Note) 1. Measuring methods are based JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. Electrostatic breakdown voltage is ±10 kV

Test method: IEC1000-4-2 (C = 150 pF, R = 330  $\Omega$ , Contact discharge: 10 times)

3. \*: The temperature must be controlled 25°C for V<sub>Z</sub> mesurement.

 $V_Z$  value measured at other temperature must be adjusted to  $V_Z\,(25^{\circ}\text{C})$ 

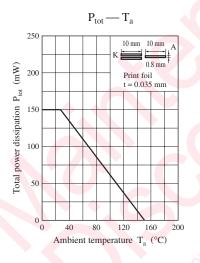
 $\ensuremath{V_{Z}}$  guaranted 20 ms after current flow.

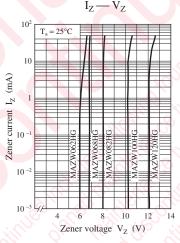
#### ■ Electrical characteristics within part numbers $T_a = 25$ °C $\pm 3$ °C

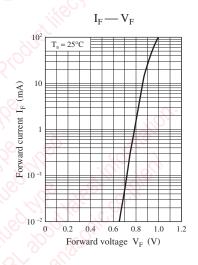
	Zener voltage			Reverse current (DC)		Zener operating resistance			
Part number	V <sub>Z</sub> (V)		I <sub>R</sub> (μA)		$R_{Z}(\Omega)$	$R_{ZK}(\Omega)$	Marking symbol		
	N di-	Name	Mari	I <sub>Z</sub>	Mari	V <sub>R</sub>	-	$I_Z = 0.5 \text{ mA}$	
	Min	Nom	Max	(mA)	Max	(V)	Max	Max	
MAZW062HG	5.8	6.2	6.6	5	0.2	4	50	100	62
MAZW068HG	6.4	6.8	7.2	5	0.1	4	30	60	68
MAZW082HG	7.7	8.2	8.7	5	0.1	5	30	60	82
MAZW100HG	9.4	10.0	10.6	5	0.05	7	30	60	10
MAZW120HG	11.4	12.0	12.7	5	0.05	9	30	60	12

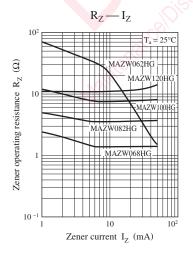
Note) 1. The  $V_Z$  value is the one after power application for 20 ms at  $T_a = 25$ °C.

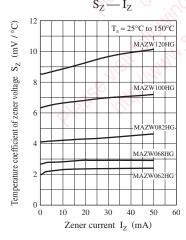
2. The zener voltage temperature coefficient is the one for  $T_j = 25$ °C to 150°C.

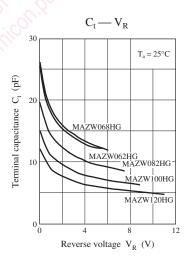






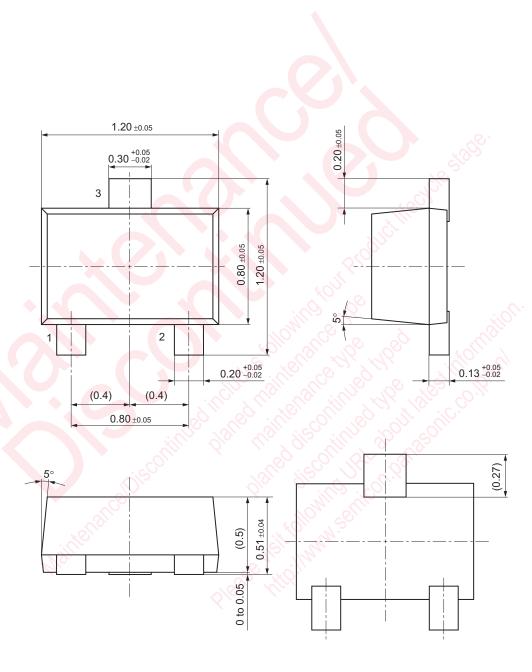






SSSMini3-F2

Unit: mm



3 SKE00035AED

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